

### SILICON PRESS-FIT DIODES

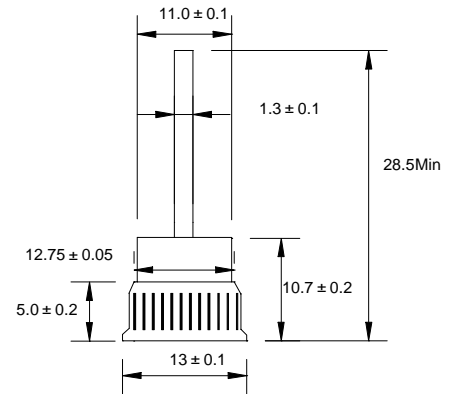
VOLTAGE RANGE: 200 -- 600 V

CURRENT: 50 A

### FEATURES

- ◇ Norminal current 50A
- ◇ Repetitive peak reverse voltage 600 V
- ◇ Metal press -fit case with plastic cover

### ZQL2



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

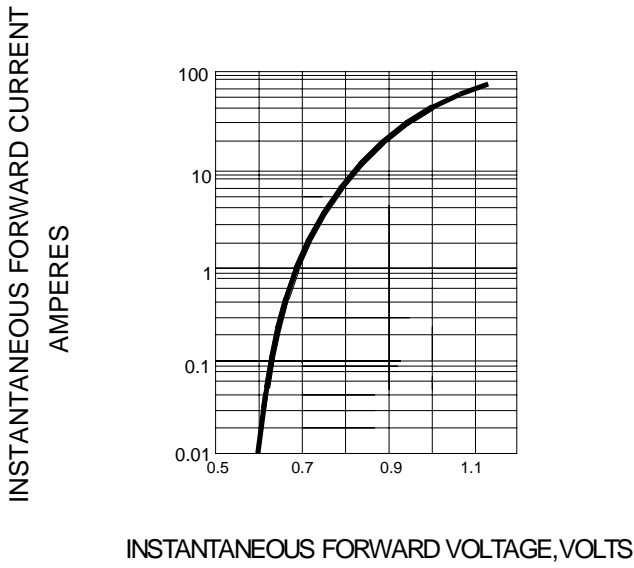
Ratings at 25°C ambient temperature unless otherwise specified.

Wire to anode		ZQ50A2L2	ZQ50A4L2	ZQ50A6L2	UNITS
Wire to cathode		ZQ50K2L2	ZQ50K4L2	ZQ50K6L2	
Repetitive peak reverse voltage	$V_{RRM}$	200	400	600	V
Surge peak reverse voltage	$V_{RSM}$	240	480	700	V
Max.average forward rectified current, R-load @ $T_A=55^\circ\text{C}$	$I_{F(AV)}$	50			A
Repetitive peak forward current $f > 15\text{Hz}$ (NOTE1)	$I_{FRM}$	110			A
Peak forward surge current,50/60 Hz half sine-wave	$I_{FSM}$	450/500			A
Forward voltage @ $I_F=50\text{A}$	$V_F$	1.1			V
Leakage current @ $T_j=25^\circ\text{C}$	$I_R$	100			$\mu\text{A}$
Rating for fusing $t < 10\text{ms}$	$i^2t$	800			$\text{A}^2\text{S}$
Thermal resistance junction to case	$R_{thc}$	0.7			K/W
Operating junction temperature	$T_j$	- 55 --- + 215			$^\circ\text{C}$
Storage temperature range	$T_s$	- 55 --- + 215			$^\circ\text{C}$

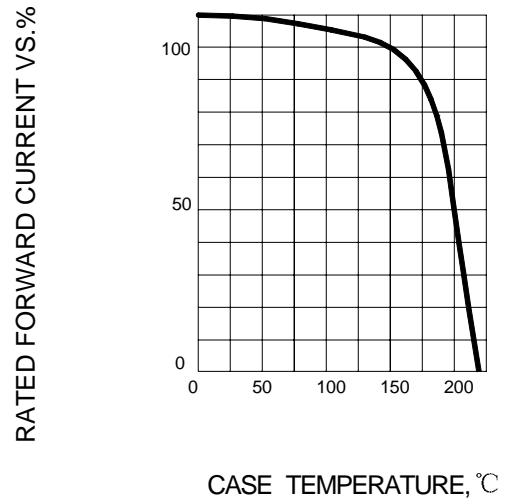
NOTE: Max.case temperature  $T_c=150^\circ\text{C}$ -Max.

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**FIG.1 – TYPICAL FORWARD CHARACTERISTIC**



**FIG.2 – FORWARD DERATING CURRENT**



**FIG.3 – PEAK FORWARD SURGE CURRENT**

